

2SC2216 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 300 mW ($T_{amb}=25^{\circ}C$)

Collector current

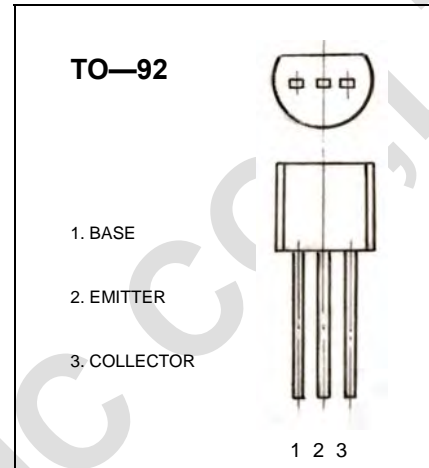
I_{CM} : 50 mA

Collector-base voltage

$V_{(BR)CBO}$: 50 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10 mA, I_B=0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=50 V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3 V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=12.5V, I_C=12.5 mA$	40		140	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=15mA, I_B=1.5 mA$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=15mA, I_B=1.5 mA$			1.5	V
Transition frequency	f_T	$V_{CE}=12.5 V, I_C=12.5mA$ $f=100 MHz$	300			MHz